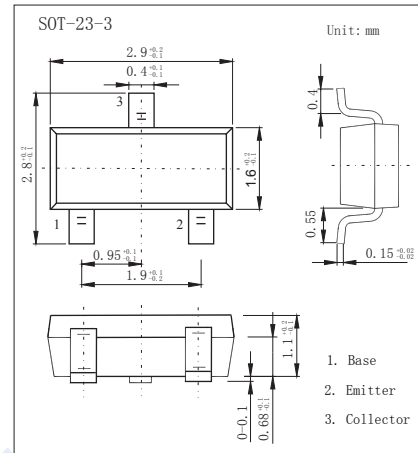


NPN Transistors

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■ Features

- Collector Current Capability $I_c=30\text{mA}$
- Collector Emitter Voltage $V_{CE0}=20\text{V}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	25	V
Collector - Emitter Voltage	V_{CE0}	20	
Emitter - Base Voltage	V_{EB0}	3	
Collector Current - Continuous	I_c	30	mA
Collector Power Dissipation	P_c	150	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}, I_E = 0$	25			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1 \text{mA}, I_B = 0$	20			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_c = 0$	3			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 10\text{V}, I_E = 0$			0.1	uA
Emitter cut-off current	I_{EB0}	$V_{EB} = 3\text{V}, I_c = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 30 \text{mA}, I_B = 3 \text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 30 \text{mA}, I_B = 3 \text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6\text{V}, I_c = 1 \text{mA}$	40		180	
Base time constant	$r_{bb'} C_c$	$V_{CB} = 6\text{V}, I_c = 1 \text{mA}, f = 31.9 \text{MHz}$			19	ps
Noise figure	NF	$V_{CE} = 6\text{V}, I_c = 1 \text{mA}, f = 100 \text{MHz}$		2.2		dB
Power gain	PG	$V_{CE} = 6\text{V}, I_c = 1 \text{mA}, f = 100 \text{MHz}$		28		
Reverse transfer capacitance	C_{re}	$V_{CB} = 6\text{V}, f = 1 \text{MHz}$			0.9	pF
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_c = 4 \text{mA}$	450			MHz

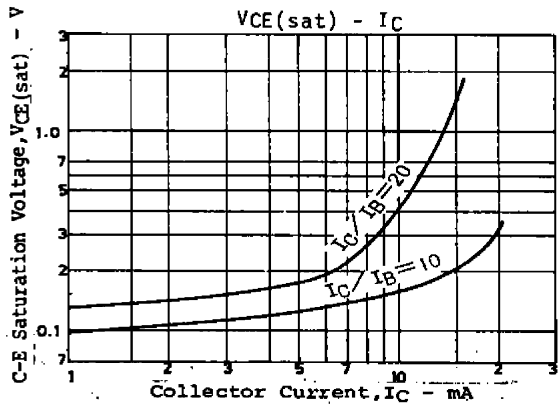
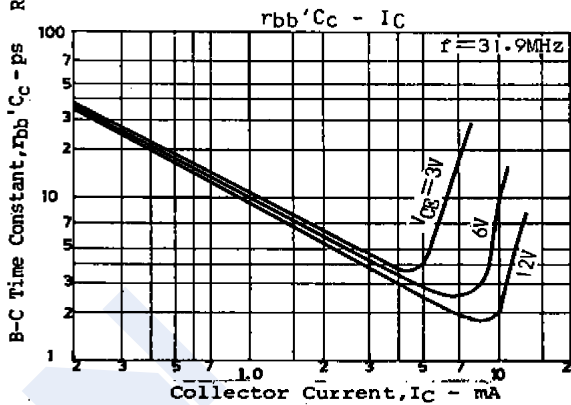
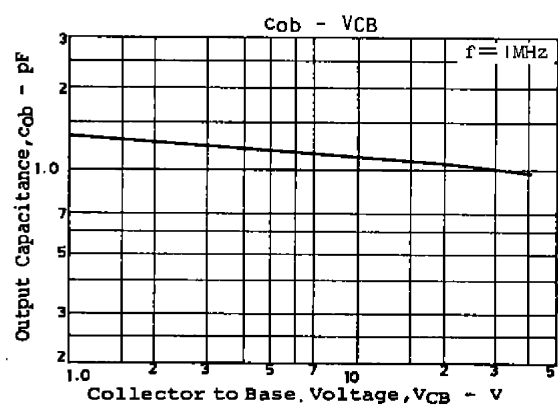
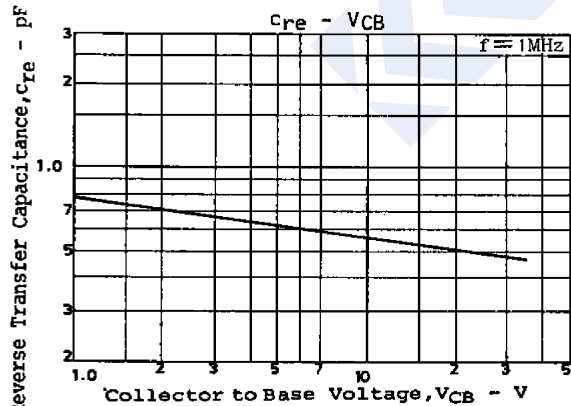
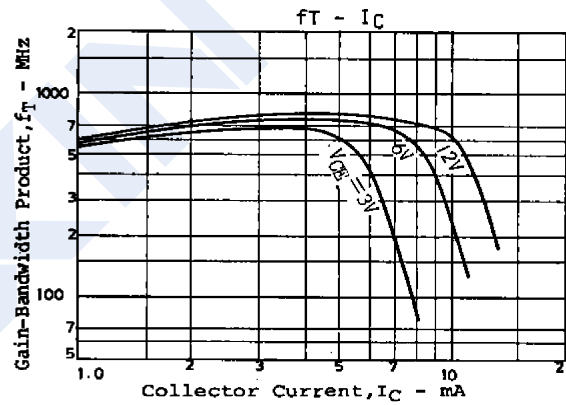
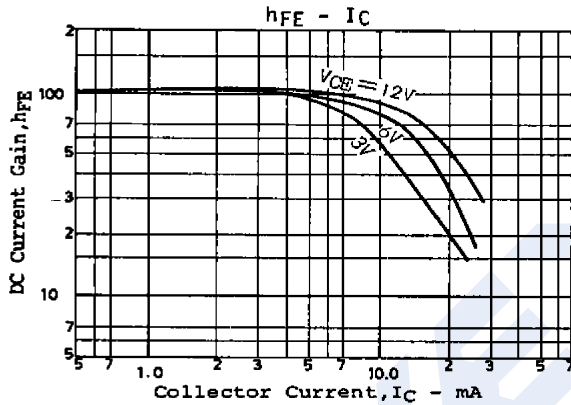
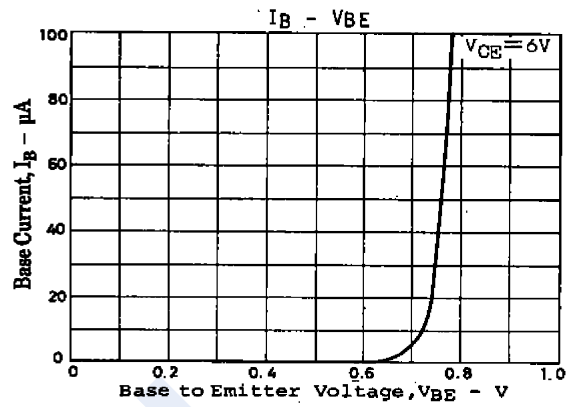
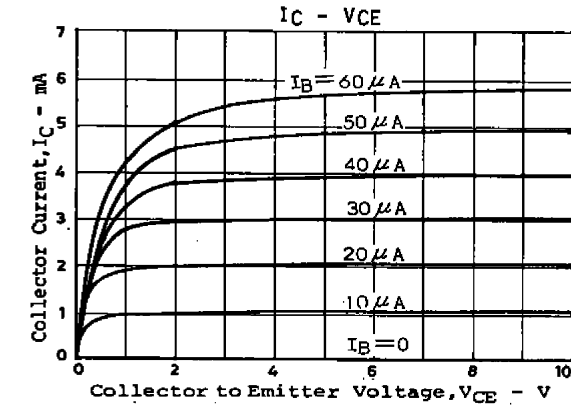
■ Classification of h_{FE}

Type	2SC3142-J2	2SC3142-J3	2SC3142-J4
Range	40-80	60-120	90-180
Marking	J2	J3	J4

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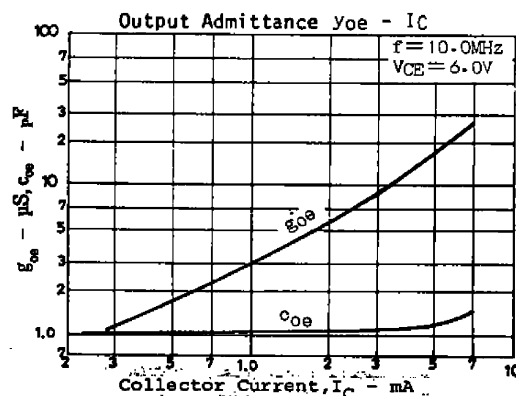
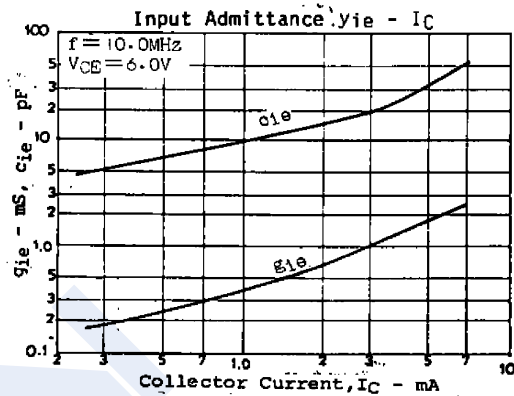
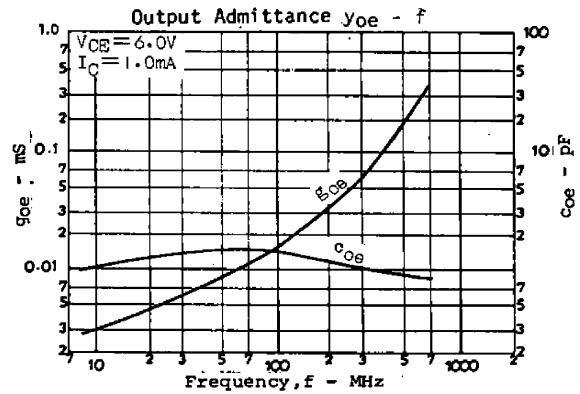
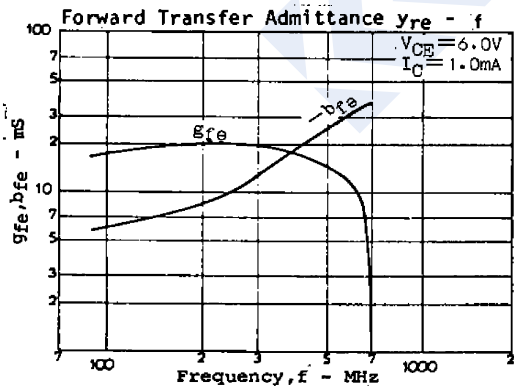
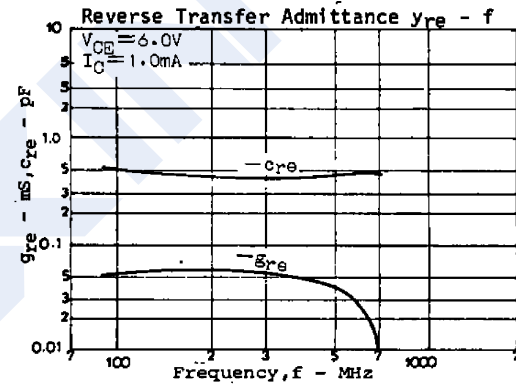
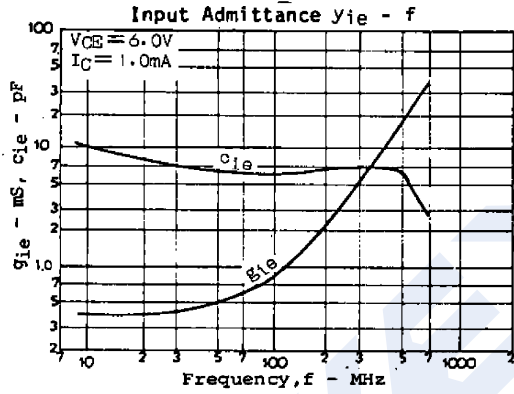
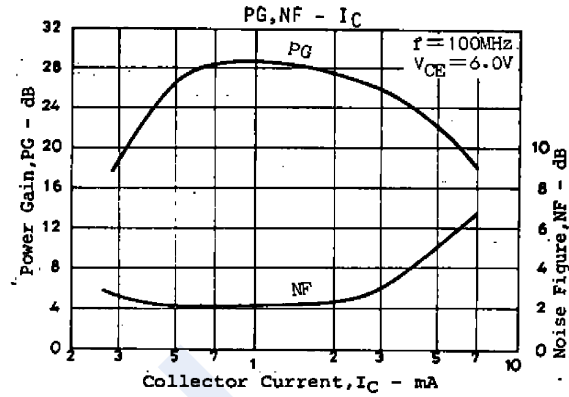
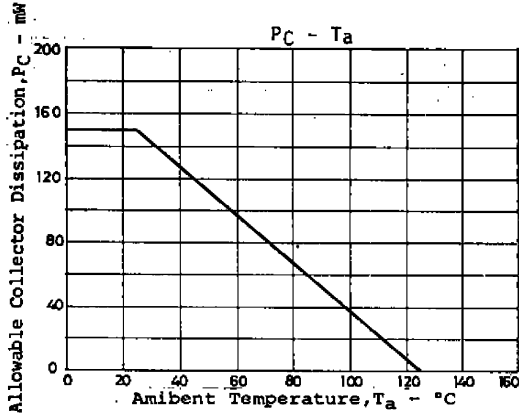
■ Typical Characteristics



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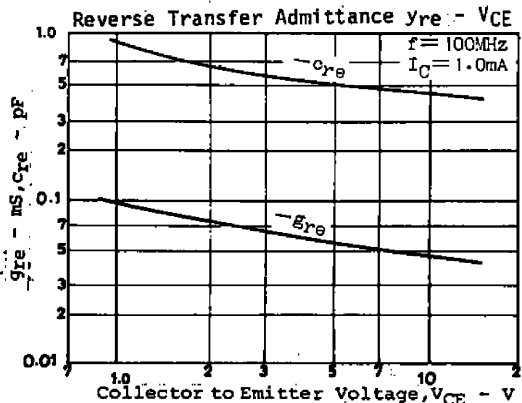
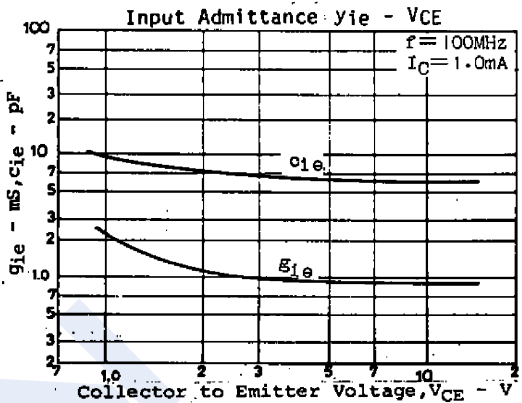
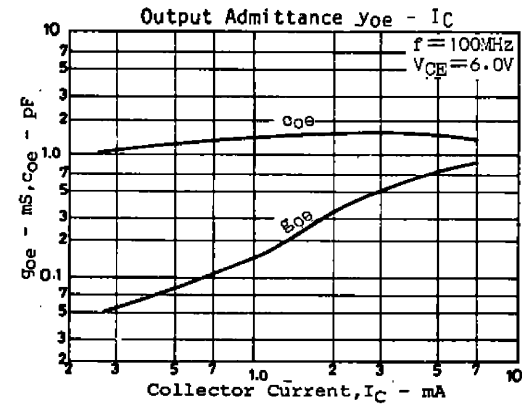
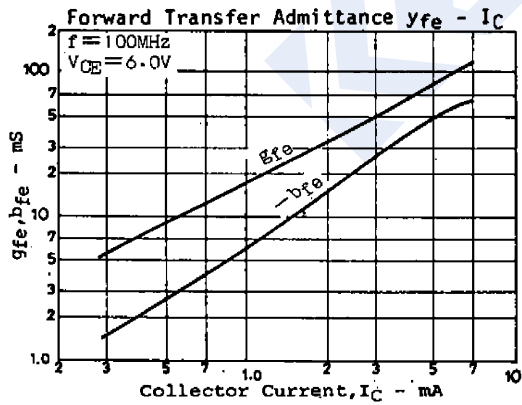
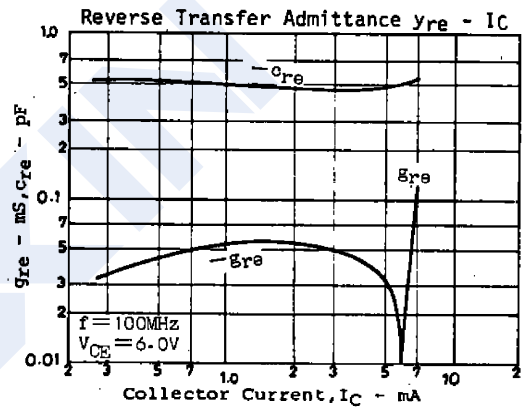
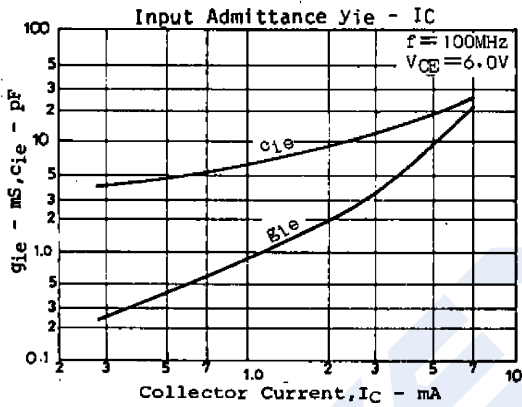
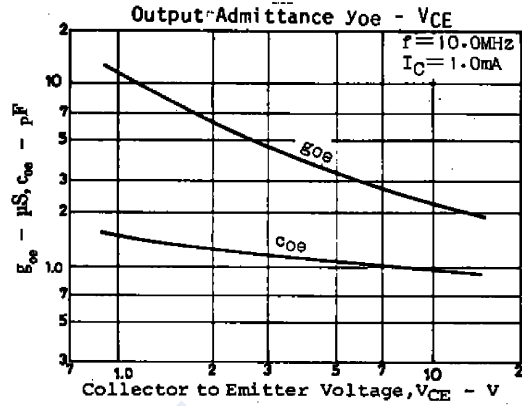
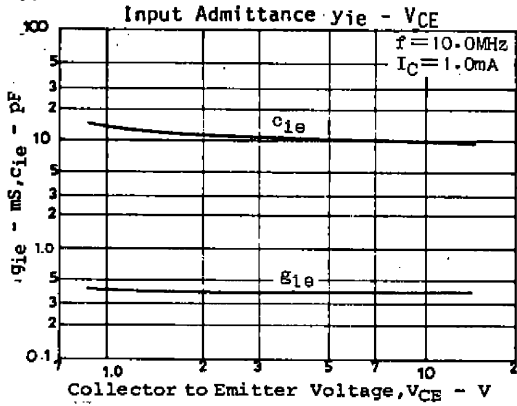
■ Typical Characteristics



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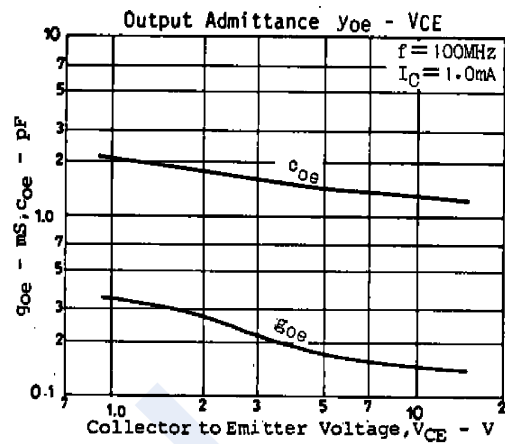
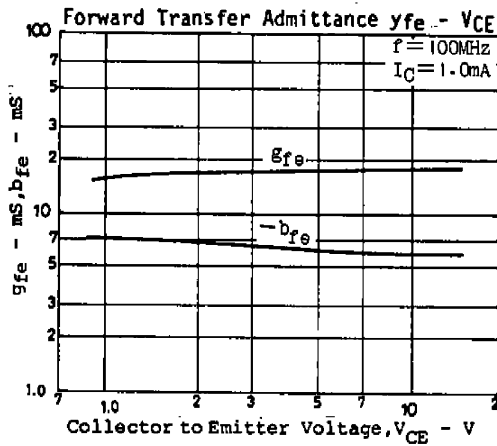
■ Typical Characteristics



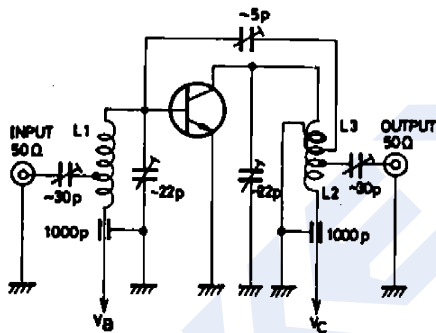
NPN Transistors

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■ Typical Characteristics



NF, PG Test Circuit



L1: 1mm ϕ plated wire 10mm ϕ 5T, pitch 15mm, tap: 2T from base.

L2: 1mm ϕ plated wire 10mm ϕ 7T, pitch 10mm, tap: 2T from V_C .

L3: 1mm ϕ enameled wire 10mm ϕ 3T, pitch 10mm.

Unit (Capacitance : F)